

2SK2339

Silicon N-Channel Power F-MOS

■ Features

- Avalanche energy capability guaranteed
- Low ON-resistance
- No secondary breakdown
- Low-voltage drive

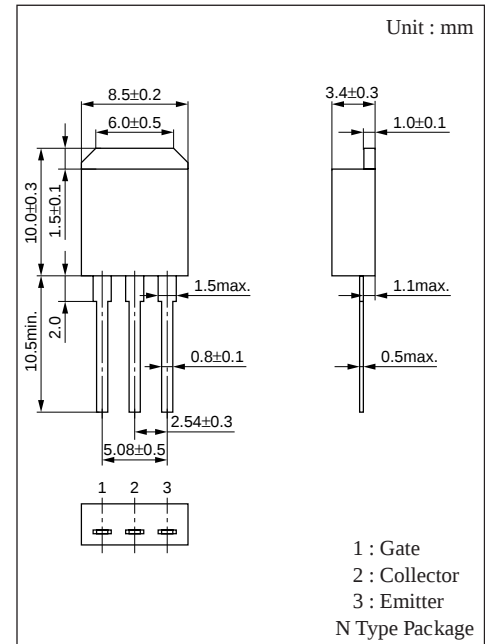
■ Applications

- Non-contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

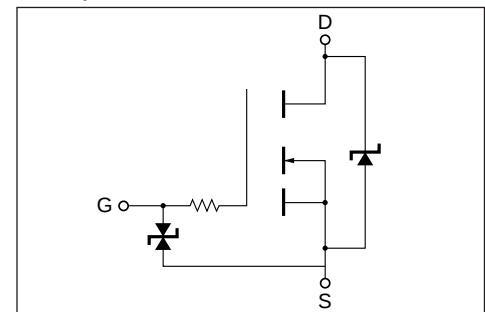
■ Absolute Maximum Ratings (T_c = 25°C)

Parameter	Symbol	Rating	Unit
Drain-Source breakdown voltage	V _{DSS}	80±10	V
Gate-Source voltage	V _{GSS}	±15	V
Drain current	DC	I _D	±10
	Pulse	I _{DP}	±20
Avalanche energy capability	EAS *	62.5	mJ
Allowable power dissipation	T _C = 25°C	P _D	30
	T _a = 25°C		1.3
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* L = 5mH, I_L = 5A, 1 pulse



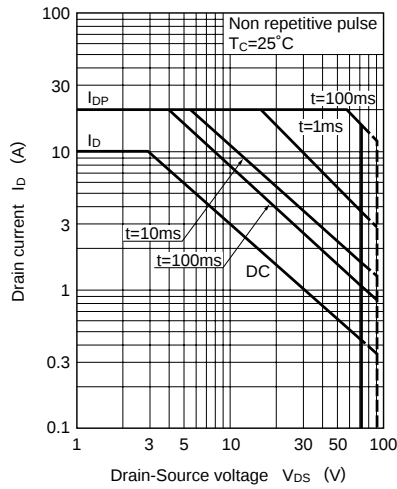
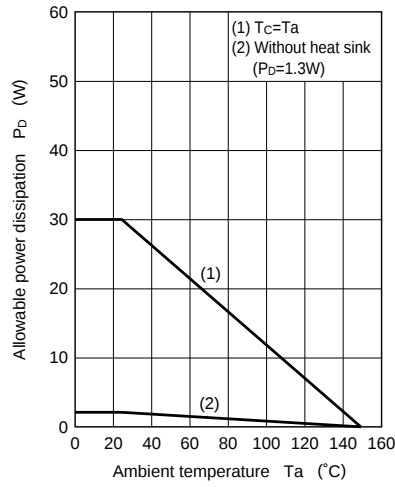
■ Equivalent Circuit



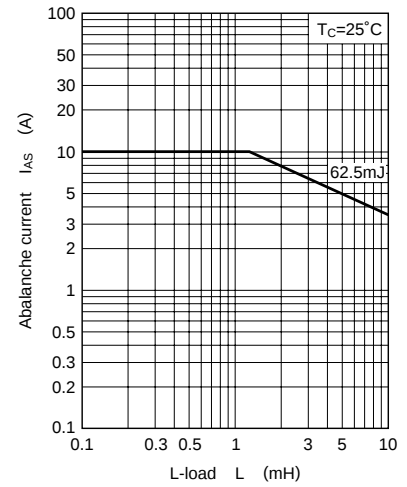
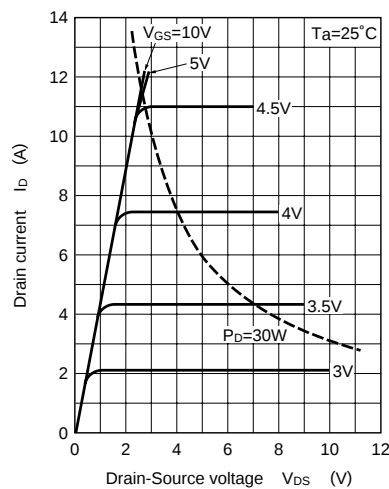
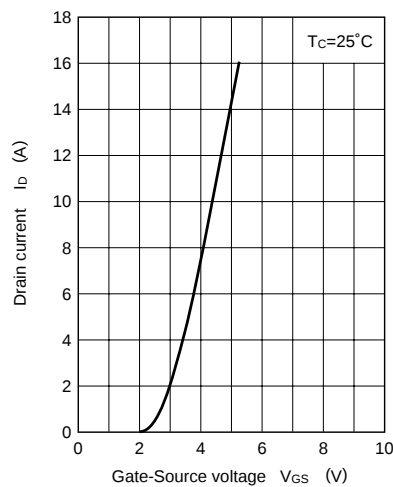
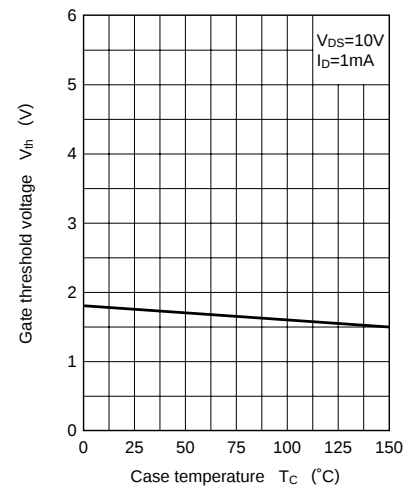
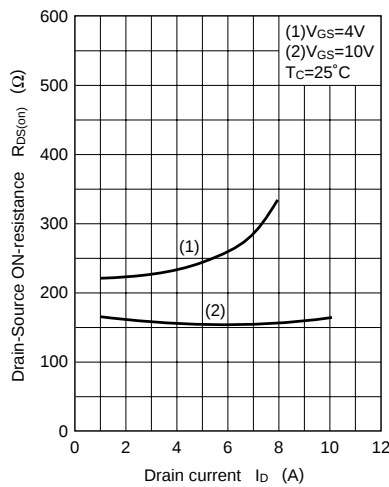
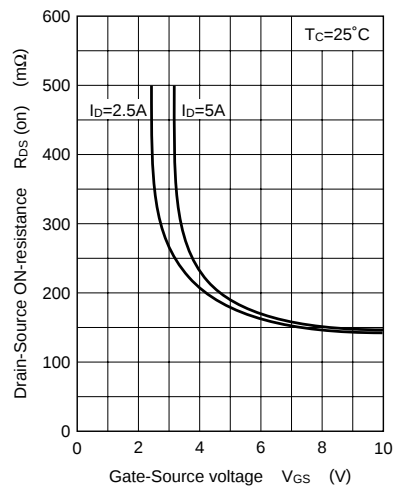
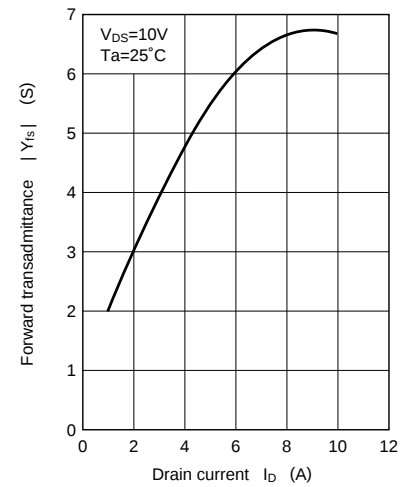
■ Electrical Characteristics (T_c = 25°C)

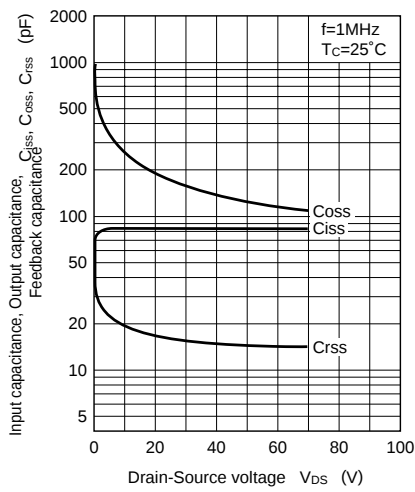
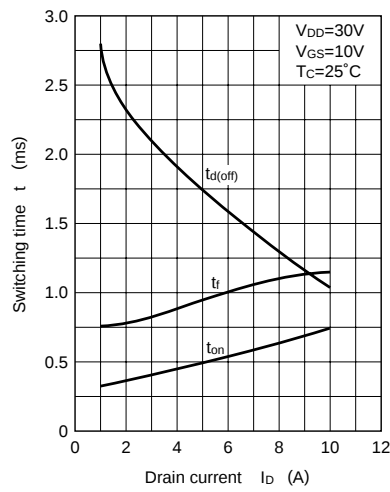
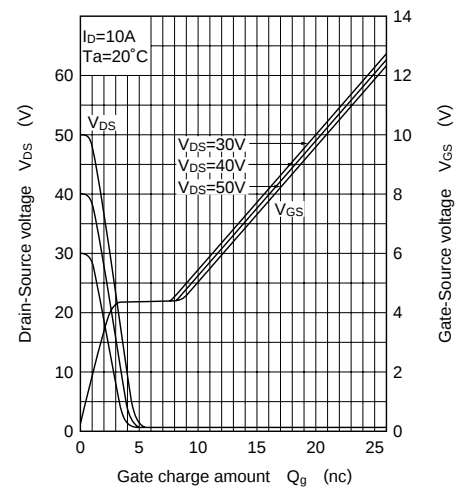
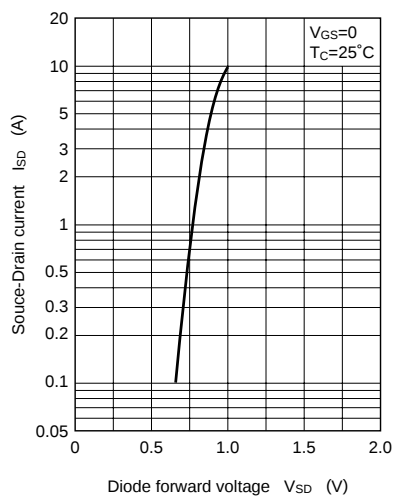
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source cut-off current	I _{DSS}	V _{DS} = 70V, V _{GS} = 0			10	μA
Gate-Source leakage current	I _{GSS}	V _{DS} = 0, V _{GS} = 15V			±10	μA
Drain-Source breakdown voltage	V _{DSS}	I _D = 1mA, V _{GS} = 0	70		90	V
Gate threshold voltage	V _{th}	V _{DS} = 10V, I _D = 1mA	1		2.5	V
Drain-Source ON-resistance	R _{DS(on)1}	V _{GS} = 10V, I _D = 5A		150	230	mΩ
	R _{DS(on)2}	V _{GS} = 4V, I _D = 5A		230	370	mΩ
Forward transadmittance	Y _{fs}	V _{DS} = 10V, I _D = 5A	3	5.5		S
Diode forward voltage	V _{DSF}	I _{DR} = 10A, V _{GS} = 0			-1.8	V
Reverse recovery time	t _{rr}	L = 230μH, V _{DD} = 30V, V _{GS} = 0		0.55		μs
Reverse recovery charge	Q _{rr}	I _{DR} = 10A, di/dt = 80A/μs		2.2		μs
Input capacitance	C _{iss}	V _{DS} = 10V, V _{GS} = 0, f = 1MHz		85		pF
Output capacitance	C _{oss}			250		pF
Feedback capacitance	C _{rss}			20		pF
Turn-on time	t _{on}			0.5		μs
Fall time	t _f	V _{DD} = 30V, I _D = 5A		0.9		μs
Turn-off time (delay time)	t _{d(off)}	V _{GS} = 10V, R _L = 6Ω		1.9		μs
Channel-Case heat resistance	R _{th(ch-c)}				4.2	°C/W
Channel-Atmosphere heat resistance	R _{th(ch-a)}				96	°C/W

Area of safe operation (ASO)

 $P_D - T_a$ 

IAS – L-load

 $I_D - V_{DS}$  $I_D - V_{GS}$  $V_{th} - T_C$  $R_{DS(on)} - I_D$  $R_{DS(on)} - V_{GS}$  $|Y_{fs}| - I_D$ 

$C_{iss}, C_{oss}, C_{rss} - V_{DS}$  $t_{d(off)}, t_r, t_{on} - I_D$  $V_{DS}, V_{GS} - Q_g$  $I_{SD} - V_{SD}$  $R_{th} - t_p$ 